

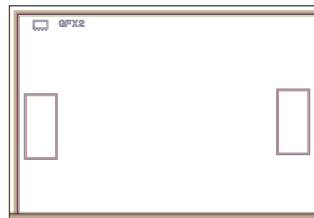
Low Noise, Wideband, High IP3 Monolithic Amplifier Die

PMA3-83LNW-D+

50Ω 0.4 to 8 GHz

The Big Deal

- Flat gain over wideband, 0.4 to 8 GHz
- Low noise figure, 1.2 dB
- High IP3, up to +37 dBm



Product Overview

The PMA3-83LNW-D+ is a PHEMT based wideband, low noise MMIC amplifier die with a unique combination of low noise, high IP3, and flat gain over wideband making it ideal for sensitive, high-dynamic-range receiver applications. This design operates on a single 5V or 6V supply, is well matched for 50Ω.

Key Features

| Feature | Advantages |
|---|---|
| Low noise, 1.2 dB at 2 GHz | Enables lower system noise figure performance. |
| High IP3 <ul style="list-style-type: none">• +37 dBm at 2 GHz• +29 dBm at 8 GHz | Combination of low noise and high IP3 makes this MMIC amplifier ideal for use in low noise receiver front end (RFE) as it gives the user advantages of sensitivity and two-tone IM performance at both ends of the dynamic range. |
| Low operating voltage, 5V/6V. | Achieves high IP3 using low voltage. |
| Wide bandwidth with flat gain <ul style="list-style-type: none">• ±0.6 dB over 0.4 to 7 GHz• ±1.5 dB over 0.4 to 8 GHz | Enables a single amplifier to be used in many wideband applications including defense, instrumentation and more. |
| Unpackaged die | Enables user to integrate it directly into hybrids. |

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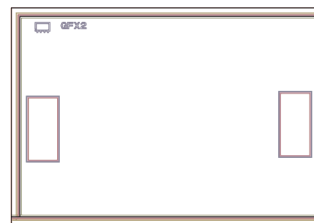
50Ω 0.4 to 8 GHz

Product Features

- Low Noise figure, 1.2 dB at 2 GHz
- High IP3, 31 dBm typ. at 2 GHz
- High Pout, P1dB 21.7 dBm typ. at 2 GHz and 6V
- Excellent Gain flatness, ±0.6 dB over 0.4 to 7 GHz and 6V

Typical Applications

- WiFi
- WLAN
- UMTS
- LTE
- WiMAX
- S-band Radar
- C-band Satcom



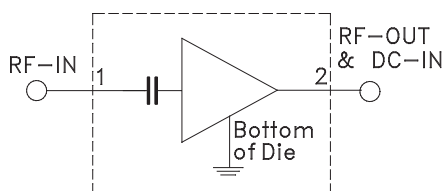
+RoHS Compliant
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

Ordering Information: Refer to Last Page

General Description

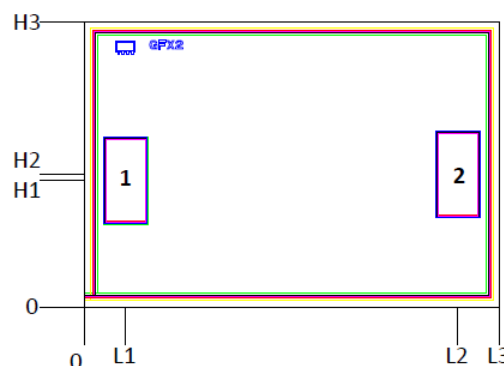
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Simplified Schematic and Pad description



| Pad# | Function |
|---------------|------------------|
| 1 | RF-IN |
| 2 | RF-OUT AND DC-IN |
| Bottom of Die | GND |

Bonding Pad Position



Dimensions in μm, Typical

| L1 | L2 | L3 | H1 | H2 | H3 | Thickness | Die size | Pad size 1 | Pad size 2 |
|----|-----|-----|-----|-----|-----|-----------|----------|------------|------------|
| 97 | 865 | 962 | 292 | 306 | 660 | 100 | 660X962 | 101X201 | 101X201 |



Electrical Specifications¹ at 25°C, unless noted

| Parameter | Condition (GHz) | V _{DD} =6.0 | | | V _{DD} =5.0 | | | Units |
|---|-----------------|----------------------|-------|------|----------------------|-------|------|-------|
| | | Min. | Typ. | Max. | Min. | Typ. | Max. | |
| Frequency Range | | 0.4 | | 8.0 | 0.4 | | 8.0 | GHz |
| Noise Figure | 0.4 | | 2.0 | | | 2.0 | | dB |
| | 2.0 | | 1.2 | | | 1.2 | | |
| | 4.0 | | 1.3 | | | 1.4 | | |
| | 5.0 | | 1.5 | | | 1.6 | | |
| | 8.0 | | 2.2 | | | 2.2 | | |
| Gain | 0.4 | | 22.0 | | | 21.1 | | dB |
| | 2.0 | | 22.6 | | | 21.7 | | |
| | 4.0 | | 21.8 | | | 21.0 | | |
| | 5.0 | | 21.3 | | | 20.6 | | |
| | 8.0 | | 19.0 | | | 18.6 | | |
| Input Return Loss | 0.4 | | 10 | | | 10 | | dB |
| | 2.0 | | 17 | | | 18 | | |
| | 4.0 | | 12 | | | 11 | | |
| | 5.0 | | 11 | | | 10 | | |
| | 8.0 | | 7 | | | 7 | | |
| Output Return Loss | 0.4 | | 22 | | | 22 | | dB |
| | 2.0 | | 14 | | | 16 | | |
| | 4.0 | | 24 | | | 24 | | |
| | 5.0 | | 19 | | | 18 | | |
| | 8.0 | | 10 | | | 9 | | |
| Output Power at 1dB Compression | 0.4 | | 18.8 | | | 16.2 | | dBm |
| | 2.0 | | 21.7 | | | 20.5 | | |
| | 4.0 | | 20.4 | | | 18.9 | | |
| | 5.0 | | 20.2 | | | 18.8 | | |
| | 8.0 | | 18.1 | | | 17.3 | | |
| Output IP3 | 0.4 | | 32.2 | | | 28.7 | | dBm |
| | 2.0 | | 37.0 | | | 31.1 | | |
| | 4.0 | | 34.5 | | | 30.1 | | |
| | 5.0 | | 32.0 | | | 28.6 | | |
| | 8.0 | | 29.0 | | | 26.8 | | |
| Device Operating Voltage (V _{DD}) | | 5.75 | 6 | 6.25 | 4.75 | 5 | 5.25 | V |
| Device Operating Current (I _{DD}) | | | 75 | 94 | | 58 | | mA |
| Device Current Variation vs. Temperature ² | | | -190 | | | -143 | | µA/°C |
| Device Current Variation vs. Voltage | | | 0.017 | | | 0.017 | | mA/mV |
| Thermal Resistance, junction-to-ground lead | | | 47 | | | 47 | | °C/W |

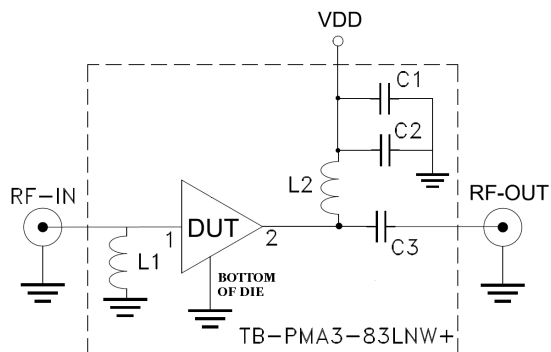
1. Measured on Mini-Circuits Characterization test board. Die is packaged in 3X3 mm, 12-lead MCL package and soldered on TB-PMA3-83LNW+. See Characterization Test Circuit (Fig. 1)
 2. (Current at 105°C - Current at -45°C)/130

Absolute Maximum Ratings³

| Parameter | Ratings |
|--|--|
| Operating Temperature (ground lead) | -40°C to 105°C |
| Junction Temperature | 150°C |
| Total Power Dissipation | 0.95 W |
| Input Power (CW), V _d =5,6V | +19 dBm (5 minutes max) +9 dBm (continuous, 0.4-0.5 GHz) +16 dBm (continuous, 0.5-8 GHz) |
| DC Voltage | 7 V |

3. Permanent damage may occur if any of these limits are exceeded.
 Electrical maximum ratings are not intended for continuous normal operation.

Characterization Test Circuit



| Component | Size | Value | Part Number | Manufacturer |
|-----------|------|--------|--------------------|--------------|
| L1 | 0402 | 18nH | LQP15MN18NJ02D | Murata |
| L2 | 0402 | 39nH | 0402CS-39NXGLW | Coilcraft |
| C1 | 0402 | 0.01uF | GRM155R71E103KA01D | Murata |
| C2 | 0402 | 10pF | GJM1555C1H100JB01D | Murata |
| C3 | 0402 | 100pF | GRM1555C1H101JA01D | Murata |

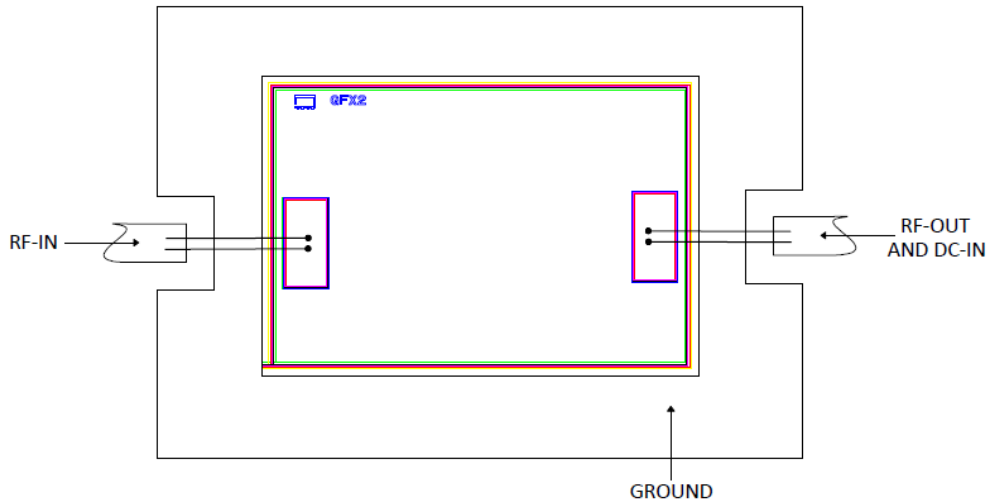
Fig 1. Application and Characterization Circuit

Note: This block diagram is used for characterization. (Die is packaged in 3x3mm, 12-lead MCLP package and soldered on Mini-Circuits Characterization test board TB-PMA3-83LNW+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.

Assembly Diagram



Assembly and Handling Procedure

1. Storage
Dice should be stored in a dry nitrogen purged desiccators or equivalent.
2. ESD
MMIC PHEMT amplifier dice are susceptible to electrostatic and mechanical damage. Dice are supplied in antistatic protected material, which should be opened in clean room conditions at an appropriately grounded anti-static workstation. Devices need careful handling using correctly designed collets, vacuum pickup tips or sharp antistatic tweezers to deter ESD damage to dice.
3. Die Attach
The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are DieMat DM6030HK-PT/H579 or Ablestik 84-1LMISR4. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total die periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. It is recommended to use antistatic die pick up tools only.
4. Wire Bonding
Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermosonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1 mil diameter. Bonds must be made from the bond pads on the die to the package or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.

| Additional Detailed Technical Information <i>additional information is available on our dash board.</i> | |
|---|---|
| Performance Data | Data Table |
| | Swept Graphs |
| | S-Parameter (S2P Files) Data Set with and without port extension(.zip file) |
| Case Style | Die |
| Die Ordering and packaging information | Quantity, Package Model No. |
| | Small, Gel - Pak: 5,10,50,100 KGD* PMA3-83LNW-DG+ Medium†, Partial wafer: KGD*<1911 PMA3-83LNW-DP+ Large†, Full Wafer PMA3-83LNW-DF+ |
| | †Available upon request contact sales representative |
| | Refer to AN-60-067 |
| Environmental Ratings | ENV80 |

*Known Good Dice ("KGD") means that the dice in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such dice fall within a predefined range. While DC testing is not definitive, it does help to provide a higher degree of confidence that dice are capable of meeting typical RF electrical parameters specified by Mini-Circuits.

ESD Rating**

Human Body Model (HBM): Class 1A (250 to <500V) in accordance with ANSI/ESD STM 5.1 - 2001

** Tested in industry standard MCLP 3x3 mm, 12-lead package.

Additional Notes

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